

ABSTRACT

A photodiode array 1 is provided with an n-type silicon substrate 3. A plurality of photodiodes 4 are formed in array on the opposite surface side to an incident surface of light L to be detected, in the n-type silicon substrate 3. A depression 6 with a predetermined depth more depressed than a region not corresponding to regions where the photodiodes 4 are formed is formed in regions corresponding to the regions where the photodiodes 4 are formed, on the incident surface side of the light L to be detected, in the n-type silicon substrate 3.

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